

HEFEI HEJING ELECTRONICS CO.LTD

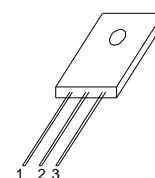
HJ 13002

NPN EPITAXIAL SILICON

TRANSISTOR

Absolute Maximum Ratings ( $T_a=25$  )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	600	V
Collector-Emitter Voltage	$V_{CE0}$	400	V
Emitter-Base Voltage	$V_{EB0}$	7	V
Collector Current	$I_C$	0.75	A
Collector Power Dissipation	$P_C$	15	W
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55~ 150	



1, B 2, C 3, E

TO-126

Electrical Characteristic ( $T_a=25$  )

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Voltage	$V_{CB0}$	$I_C=1mA$	600			V
Collector-Emitter Voltage	$V_{CE0}$	$I_C=10mA$	400			V
Emitter-Base Voltage	$V_{EB0}$	$I_E=1mA$	7			V
DC Current Gain	$h_{FE}$	$V_{CE}=10V, I_C=0.1A$	10		40	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=0.5A$ $I_B=0.1A$			0.8	V

$h_{FE}$  Classification:    10~ 15    15~ 20    20~ 25    25~ 30  
                                   30~ 35    35~ 40